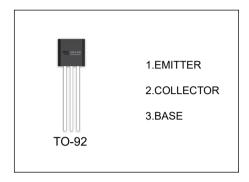


A733 TRANSISTOR (PNP)

FEATURE

Power dissipation



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
A733	TO-92	Bulk	1000pcs/Bag
A733-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-100	mA
Pc	Collector Power Dissipation	250	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}$



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -50uA,I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA , I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -50uA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -60V, I _E =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -5 V, I _C =0			-0.1	uA
DC current gain	h _{FE}	V _{CE} = -6V, I _C = -1mA	90	200	600	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = -100mA, I _B =- 10mA		-0.18	-0.3	V
Base-emitter voltage	V _{BE}	V _{CE} =-6V,I _C =-1.0mA	-0.58	-0.62	-0.68	V
Transition frequency	f _T	V _{CE} =-6V,I _C =-10mA	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V,I _E =0,f=1MH _Z			6	pF
Noise figure	NF	V_{CE} =-6V, I_{C} =-0.3mA, Rg=10k Ω ,f=100H $_{Z}$			20	dB

CLASSIFICATION OF h_{FE}

Rank	R	Q	Р	К
Range	90-180	135-270	200-400	300-600